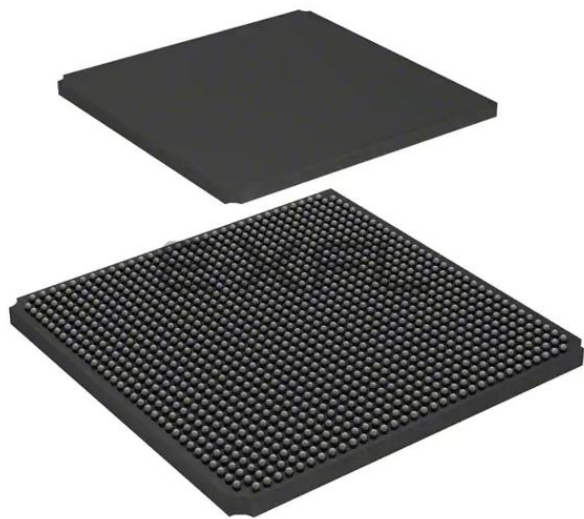




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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	512
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1152-BBGA, FCBGA
Supplier Device Package	1152-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300tl-fcg1152e

4 Device Offering

The following table lists the PolarFire FPGA device options using the MPF300T as an example. The MPF100T, MPF200T, and MPF500T device densities have identical offerings.

Table 1 • PolarFire FPGA Device Options

Device Options	Extended Commercial 0 °C–100 °C	Industrial –40 °C–100 °C	STD	–1	Transceivers T	Lower Static Power L	Data Security S
MPF300T	Yes	Yes	Yes	Yes	Yes		
MPF300TL	Yes	Yes	Yes		Yes	Yes	
MPF300TS		Yes	Yes	Yes	Yes		Yes
MPF300TLS		Yes	Yes		Yes	Yes	Yes

Parameter	Symbol	Min	Typ	Max	Unit
Transceiver TX and RX lanes supply at 1.05 V mode (when any lane rate is greater than 10.3125 Gbps) ¹	V _{DDA}	1.02	1.05	1.08	V
Programming and HSIO receiver supply	V _{DD18}	1.71	1.80	1.89	V
FPGA core and FPGA PLL high-voltage supply	V _{DD25}	2.425	2.50	2.575	V
Transceiver PLL high-voltage supply	V _{DDA25}	2.425	2.50	2.575	V
Transceiver reference clock supply –3.3 V nominal	V _{DD_XCVR_CLK}	3.135	3.3	3.465	V
Transceiver reference clock supply –2.5 V nominal	V _{DD_XCVR_CLK}	2.375	2.5	2.625	V
Global V _{REF} for transceiver reference clocks ³	XCVR _{VREF}	Ground		V _{DD_XCVR_CLK}	V
HSIO DC I/O supply. Allowed nominal options: 1.2 V, 1.35 V, 1.5 V, and 1.8 V ⁴	V _{DDI_x}	1.14	Various	1.89	V
GPIO DC I/O supply. Allowed nominal options: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V ^{2,4}	V _{DDI_x}	1.14	Various	3.465	V
Dedicated I/O DC supply for JTAG and SPI (GPIO Bank 3). Allowed nominal options: 1.8 V, 2.5 V, and 3.3 V	V _{DDI3}	1.71	Various	3.465	V
GPIO auxiliary supply for I/O bank x with V _{DDI_x} = 3.3 V nominal ^{2,4}	V _{DDAUX_x}	3.135	3.3	3.465	V
GPIO auxiliary supply for I/O bank x with V _{DDI_x} = 2.5 V nominal or lower ^{2,4}	V _{DDAUX_x}	2.375	2.5	2.625	V
Extended commercial temperature range	T _J	0		100	°C
Industrial temperature range	T _J	–40		100	°C
Extended commercial programming temperature range	T _{PRG}	0		100	°C
Industrial programming temperature range	T _{PRG}	–40		100	°C

1. V_{DD} and V_{DDA} can independently operate at 1.0 V or 1.05 V nominal. These supplies are not dynamically adjustable.
2. For GPIO buffers where I/O bank is designated as bank number, if V_{DDI_x} is 2.5 V nominal or 3.3 V nominal, V_{DDAUX_x} must be connected to the V_{DDI_x} supply for that bank. If V_{DDI_x} for a given GPIO bank is <2.5 V nominal, V_{DDAUX_x} per I/O bank must be powered at 2.5 V nominal.
3. XCVR_{VREF} globally sets the reference voltage of the transceiver's single-ended reference clock input buffers. It is typically near V_{DD_XCVR_CLK}/2 V but is allowed in the specified range.
4. The power supplies for a given I/O bank x are shown as VDDI_x and VDDAUX_x.

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Single-ended termination to $V_{SS}^{4,5}$	Internal	-20	120	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$
	parallel termination to V_{SS}	-20	240	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$

1. Measured across P to N with 400 mV bias.
2. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI} .
3. For 50 Ω /75 Ω /150 Ω cases, nearest supported values of 40 Ω /60 Ω /120 Ω are used.
4. Measured at 50% of V_{DDI} .
5. Supported terminations vary with the IO type regardless of V_{DDI} nominal voltage. Refer to Libero for available combinations.

Standard	Description	V_I^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
HSUL18I	HSUL 1.8 V Class I	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL18II	HSUL 1.8 V Class II	$V_{REF} -$ 0.54	$V_{REF} +$ 0.54			V_{REF}	0.90	V
HSUL12	HSUL 1.2 V	$V_{REF} -$.22	$V_{REF} +$.22			V_{REF}	0.60	V
POD12I	Pseudo open drain (POD) logic 1.2 V Class I	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
POD12II	POD 1.2 V Class II	$V_{REF} -$.15	$V_{REF} +$.15			V_{REF}	0.84	V
LVDS33	Low-voltage differential signaling (LVDS) 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS25	LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
LVDS18	LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
RSDS33	RSDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS25	RSDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
RSDS18	RSDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS33	Mini-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS25	Mini-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
MINILVDS18	Mini-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	1.250	0		V
SUBLVDS33	Sub-LVDS 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS25	Sub-LVDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
SUBLVDS18	Sub-LVDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.900	0		V
PPDS33	Point-to-point differential signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS25	PPDS 2.5 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
PPDS18	PPDS 1.8 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.800	0		V
SLVS33	Scalable low- voltage signaling 3.3 V	$V_{ICM} -$.125	$V_{ICM} +$.125	0.250	0.200	0		V

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	VDDAUX	VDDI	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3 ¹	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3 ¹	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3 ¹	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2 ¹	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2 ¹	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2 ¹	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	VDDAUX	VDDI	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2 ¹	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2 ¹	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T _{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew ¹	F _{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F _{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F _{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F _{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion ²	T _{DCB}	90	90	90	90	ps	HSIO without bridging
	T _{DCB}	115	115	115	115	ps	HSIO with bridging
	T _{DCB}	90	90	90	90	ps	GPIO without bridging
	T _{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2

PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{INPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDET1}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDET2}	10	50	125	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

Parameter	Symbol	Min	Typ	Max	Unit
Maximum input period clock jitter (reference and feedback clocks) ²	F _{MAXINJ}		120	1000	ps
PLL VCO frequency	F _{VCO}	800		5000	MHz
Loop bandwidth (Int) ³	F _{BW}	F _{PHDET} /55	F _{PHDET} /44	F _{PHDET} /30	MHz
Loop bandwidth (FRAC) ³	F _{BW}	F _{PHDET} /91	F _{PHDET} /77	F _{PHDET} /56	MHz
Static phase offset of the PLL outputs ⁴	T _{SPO}			Max (±60 ps, ±0.5 degrees)	ps
	T _{OUTJITTER}				ps
PLL output duty cycle precision	T _{OUTDUTY}	48		54	%
PLL lock time ⁵	T _{LOCK}			Max (6.0 μs, 625 PFD cycles)	μs
PLL unlock time ⁶	T _{UNLOCK}	2		8	PFD cycles
PLL output frequency	F _{OUT}	0.050		1250	MHz
Minimum reset pulse width	T _{MRPW}				μs
Maximum delay in the feedback path ⁷	F _{MAXDFB}			1.5	PFD cycles
Spread spectrum modulation spread ⁸	Mod_Spread	0.1		3.1	%
Spread spectrum modulation frequency ⁹	Mod_Freq	F _{PHDET} /(128x63)	32	F _{PHDET} /(128)	KHz

1. Minimum time for high or low pulse width.
2. Maximum jitter the PLL can tolerate without losing lock.
3. Default bandwidth setting of BW_PROP_CTRL = "01" for Integer and Fraction modes leads to the typical estimated bandwidth. This bandwidth can be lowered by setting BW_PROP_CTRL = "00" and can be increased if BW_PROP_CTRL = "10" and will be at the highest value if BW_PROP_CTRL = "11".
4. Maximum (±3-Sigma) phase error between any two outputs with nominally aligned phases.
5. Input clock cycle is REFDIV/F_{REF}. For example, F_{REF} = 25 MHz, REFDIV = 1, lock time = 10.0 (assumes LOCKCOUNTSEL setting = 4'd8 (256 cycles)).
6. Unlock occurs if two cycle slip within LOCKCOUNT/4 PFD cycles.
7. Maximum propagation delay of external feedback path in deskew mode.
8. Programmable capability for depth of down spread or center spread modulation.
9. Programmable modulation rate based on the modulation divider setting (1 to 63).

Note: In order to meet all data sheet specifications, the PLL must be programmed such that the PLL Loop Bandwidth < (0.0017 * VCO Frequency) – 0.4863 MHz. The Libero PLL configuration tool will enforce this rule when creating PLL configurations.

7.2.3

DLL

The following table provides information about DLL.

Table 38 • DLL Electrical Characteristics

Parameter ¹	Symbol	Min	Typ	Max	Unit
Input reference clock frequency	F _{INF}	133		800	MHz
Input feedback clock frequency	F _{INFDBF}	133		800	MHz
Primary output clock frequency	F _{OUTPF}	133		800	MHz

Table 44 • μ SRAM Performance

Parameter	Symbol	$V_{DD} = 1.0\text{ V} - \text{STD}$	$V_{DD} = 1.0\text{ V} - 1$	$V_{DD} = 1.05\text{ V} - \text{STD}$	$V_{DD} = 1.05\text{ V} - 1$	Unit	Condition
Operating frequency	F_{MAX}	400	415	450	480	MHz	Write-port
Read access time	T_{ac}		2		2	ns	Read-port

Table 45 • μ PROM Performance

Parameter	Symbol	$V_{DD} = 1.0\text{ V} - \text{STD}$	$V_{DD} = 1.0\text{ V} - 1$	$V_{DD} = 1.05\text{ V} - \text{STD}$	$V_{DD} = 1.05\text{ V} - 1$	Unit
Read access time	T_{ac}	10	10	10	10	ns

7.4 Transceiver Switching Characteristics

This section describes transceiver switching characteristics.

7.4.1 Transceiver Performance

The following table describes transceiver performance.

Table 46 • PolarFire Transceiver and TXPLL Performance

Parameter	Symbol	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit
Tx data rate ^{1,2}	F_{TXRate}	0.25		10.3125	0.25		12.7	Gbps
Tx OOB (serializer bypass) data rate	$F_{TXRateOOB}$	DC		1.5	DC		1.5	Gbps
Rx data rate when AC coupled ²	$F_{RxRateAC}$	0.25		10.3125	0.25		12.7	Gbps
Rx data rate when DC coupled	$F_{RxRateDC}$	0.25		3.2	0.25		3.2	Gbps
Rx OOB (deserializer bypass) data rate	$F_{TXRateOOB}$	DC		1.25	DC		1.25	Gbps
TXPLL output frequency ³	F_{TXPLL}	1.6		6.35	1.6		6.35	GHz
Rx CDR mode	F_{RXCDR}	0.25		10.3125	0.25		10.3125	Gbps
Rx DFE mode ²	F_{RXDFE}	3.0		10.3125	3.0		12.7	Gbps
Rx Eye Monitor mode ²	$F_{RXEyeMon}$	3.0		10.3125	3.0		12.7	Gbps

1. The reference clock is required to be a minimum of 75 MHz for data rates of 10 Gbps and above.
2. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6).
3. The Tx PLL rate is between 0.5x to 5.5x the Tx data rate. The Tx data rate depends on per XCVR lane Tx post-divider settings.

7.4.2 Transceiver Reference Clock Performance

The following table describes performance of the transceiver reference clock.

Table 47 • PolarFire Transceiver Reference Clock AC Requirements

Parameter	Symbol	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit
Reference clock input rate ^{1,2}	$F_{TXREFCLK}$	20		800	20		800	MHz

Parameter	Modes ¹	STD Min	STD Max	-1 Min	-1 Max	Unit
Transceiver RX_CLK range (non- deterministic PCS mode with global or regional fabric clocks)	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps		325		325	MHz
	40-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		260		320	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		130		160	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz
Transceiver TX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (–STD) / 4.25 Gbps (–1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (–STD) / 5.32 Gbps (–1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (–STD) / 8.5 Gbps (–1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (–STD) / 10.6 Gbps (–1) ¹		225		266	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		130		160	MHz
Transceiver RX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (–STD) / 4.25 Gbps (–1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (–STD) / 5.32 Gbps (–1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (–STD) / 8.5 Gbps (–1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (–STD) / 10.6 Gbps (–1) ¹		225		266	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1) ¹		130		160	MHz

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6).

Note: Until specified, all modes are non-deterministic. For more information, see [UG0677: PolarFire FPGA Transceiver User Guide](#).

Table 55 • PCI Express Gen2

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.35	UI
Receiver jitter tolerance	5.0 Gbps	0.4		UI

Note: With add-in card as specified in PCI Express CEM Rev 2.0.

7.5.2 Interlaken

The following table describes Interlaken.

Table 56 • Interlaken

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	6.375 Gbps		0.3	UI
	10.3125 Gbps		0.3	UI
	12.7 Gbps ¹			UI
Receiver jitter tolerance	6.375 Gbps	0.6		UI
	10.3125 Gbps	0.65		UI
	12.7 Gbps ¹			UI

- For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section [Recommended Operating Conditions](#) (see page 6).

7.5.3 10GbE (10GBASE-R, and 10GBASE-KR)

The following table describes 10GbE (10GBASE-R).

Table 57 • 10GbE (10GBASE-R)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps		0.28	UI
Receiver jitter tolerance	10.3125 Gbps	0.7		UI

The following table describes 10GbE (10GBASE-KR).

Table 58 • 10GbE (10GBASE-KR)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI

The following table describes 10GbE (XAUI).

Table 59 • 10GbE (XAUI)

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter (near end)	3.125 Gbps		0.35	UI
Total transmit jitter (far end)			0.55	UI
Receiver jitter tolerance	3.125 Gbps	0.65		UI

The following table describes 10GbE (RXAUI).

Table 60 • 10GbE (RXAU)

	Data Rate	Min	Max	Unit
Total transmit jitter	6.25 Gbps			UI
Receiver jitter tolerance	6.25 Gbps			UI

7.5.4**1GbE (1000BASE-T)**

The following table describes 1GbE (1000BASE-T).

Table 61 • 1GbE (1000BASE-T)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

The following table describes 1GbE (1000BASE-X).

Table 62 • 1GbE (1000BASE-X)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

7.5.5**SGMII and QSGMII**

The following table describes SGMII.

Table 63 • SGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps		0.24	UI
Receiver jitter tolerance	1.25 Gbps	0.749		UI

The following table describes QSGMII.

Table 64 • QSGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.3	UI
Receiver jitter tolerance	5.0 Gbps	0.65		UI

7.5.6**SDI**

The following table describes SDI.

Table 65 • SDI

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter				UI
Receiver jitter tolerance				UI

7.6.3 FPGA Bitstream Sizes

The following table describes FPGA bitstream sizes.

Table 72 • Initialization Client Sizes

Device	Plaintext	Ciphertext
MPF100T, TL, TS, TLS		
MPF200T, TL, TS, TLS	2916 KB	3006 KB
MPF300T, TL, TS, TLS	4265 KB	4403 KB
MPF500T, TL, TS, TLS		

Note: Worst case initializing all fabric LSRAM, USRAM, and UPROM.

Table 73 • Bitstream Sizes

File	Devices	FPGA	Security	SNVM (all pages)	FPGA+ SNVM	FPGA+ Sec	SNVM+ Sec	FPGA+ SNVM+ Sec
SPI	MPF100T, TL, TS, TLS							
DAT	MPF100T, TL, TS, TLS							
SPI	MPF200T, TL, TS, TLS	5.9 MB	3.4 KB	59.7 KB	5.9 MB	5.9 MB	62.2 KB	6.0 MB
DAT	MPF200T, TL, TS, TLS	5.9 MB	7.3 KB	61.2 KB	6.0 MB	5.9 MB	66.3 KB	6.0 MB
SPI	MPF300T, TL, TS, TLS	9.3 MB	3.5 KB	59.7 KB	9.6 MB	9.5 MB	62.2 KB	9.6 MB
DAT	MPF300T, TL, TS, TLS	9.3 MB	7.6 KB	61.2 KB	9.6 MB	9.5 MB	66.3 KB	9.6 MB
SPI	MPF500T, TL, TS, TLS							
DAT	MPF500T, TL, TS, TLS							

7.6.4 Digest Cycles

Digests verify the integrity of the programmed non-volatile data. Digests are a cryptographic hash of various data areas. Any digest that reports back an error raises the digest tamper flag.

Table 74 • Maximum Number of Digest Cycles

Retention Since Programmed (N = Number Digests During that Time) ¹										
Digest T _i	Storage and Operating T _j	N ≤300	N = 500	N = 1000	N = 1500	N = 2000	N = 4000	N = 6000	Unit	Retention
–40 to 100	–40 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 100	0 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
–40 to 85	–40 to 85	20 × LF	20 × LF	20 × LF	20 × LF	16 × LF	8 × LF	4 × LF	°C	Years
–40 to 55	–40 to 55	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	°C	Years

1. LF = Lifetime factor as defined by the number of programming cycles the device has seen under the conditions listed in the following table.

Parameter	Min	Typ	Max	Unit	Condition
Voltage sensing range	0.9		2.8	V	
Voltage sensing accuracy	–1.5		1.5	%	

Table 93 • Tamper Macro Timing Characteristics—Flags and Clearing

Parameter	Symbol	Typ	Max	Unit
From event detection to flag generation	T _{JTAG_ACTIVE} ^{1, 2}	45	52	ns
	T _{MESH_ERR} ²	1.8	2.2	μs
	T _{CLK_GLITCH} ^{1, 2}			ns
	T _{CLK_FREQ} ^{1, 2}			μs
	T _{LOW_1P05} ²	70	108	μs
	T _{HIGH_1P8} ²	85	120	μs
	T _{HIGH_2P5} ²	130	520	μs
	T _{GLITCH_1P05} ²			μs
	T _{SECDEC} ^{1, 2}			μs
	T _{DRI_ERR} ²	14	18	μs
	T _{WDOG} ^{1, 2}			μs
	T _{LOCK_ERR} ²			μs
Time from system controller instruction execution to flag generation	T _{INST_BUF_ACCESS} ^{2, 3}	4	5	μs
	T _{INST_DEBUG} ^{2, 3}	3.3	4	μs
	T _{INST_CHK_DIGEST} ^{2, 3}	1.8	3	μs
	T _{INST_EC_SETUP} ^{2, 3}	1.8	2	μs
	T _{INST_FACT_PRIV} ^{2, 3}	3.8	5	μs
	T _{INST_KEY_VAL} ^{2, 3}	2.5	3.1	μs
	T _{INST_MISC} ^{2, 3}	1.5	2	μs
	T _{INST_PASSCODE_MATCH} ^{2, 3}	2.5	3	μs
	T _{INST_PASSCODE_SETUP} ^{2, 3}	4.2	5	μs
	T _{INST_PROG} ^{2, 3}	3.8	4.1	μs
	T _{INST_PUB_INFO} ^{2, 3}	4	4.5	μs
	T _{INST_ZERO_RECO} ^{2, 3}	2.5	3	μs
	T _{INST_PASSCODE_FAIL} ^{2, 3}	170	180	μs
	T _{INST_KEY_VAL_FAIL} ^{2, 3}	92	110	μs
	T _{INST_UNUSED} ^{2, 3}	4	5	μs
Time from sending the CLEAR to deassertion on FLAG	T _{CLEAR_FLAG}	17	23	ns

1. Not available during Flash*Freeze.
2. The timing does not impact the user design, but it is useful for security analysis.
3. System service requests from the fabric will interrupt the system controller delaying the generation of the flag.

Table 94 • Tamper Macro Response Timing Characteristics

Parameter	Symbol	Typ	Max	Unit
Time from triggering the response to all I/Os disabled	T _{IO_DISABLE}	40	50	ns

Parameter	Symbol	Typ	Max	Unit
Time from negation of RESPONSE to all I/Os re-enabled	T _{CLR_IO_DISABLE}	28	38	μs
Time from triggering the response to security locked	T _{LOCKDOWN}			ns
Time from negation of RESPONSE to earlier security unlock condition	T _{CLR_LOCKDOWN}			ns
Time from triggering the response to device enters RESET	T _{tr_RESET}	11.7	14	μs
Time from triggering the response to start of zeroization	T _{tr_ZEROLISE}	7.4	8.2	ms

7.8.5 System Controller Suspend Switching Characteristics

The following table describes the characteristics of system controller suspend switching.

Table 95 • System Controller Suspend Entry and Exit Characteristics

Parameter	Symbol	Definition	Typ	Max	Unit
Time from TRSTb falling edge to SUSPEND_EN signal assertion	T _{suspend_tr} ^{1,2}	Suspend entry time from TRST_N assertion	42	44	ns
Time from TRSTb rising edge to ACTIVE signal assertion	T _{suspend_exit}	Suspend exit time from TRST_N negation	361	372	ns

1. ACTIVE indicates that the system controller is inactive or active regardless of the state of SUSPEND_EN.
2. ACTIVE signal must never be asserted with SUSPEND_EN is asserted.

7.8.6 Dynamic Reconfiguration Interface

The following table provides interface timing information for the DRI, which is an embedded APB slave interface within the FPGA fabric that does not use FPGA resources.

Table 96 • Dynamic Reconfiguration Interface Timing Characteristics

Parameter	Symbol	Max	Unit
PCLK frequency	F _{PD_PCLK}	200	MHz

7.9 Power-Up to Functional Timing

Microsemi non-volatile FPGA technology offers the fastest boot-time of any mid-range FPGA in the market. The following tables describes both cold-boot (from power-on) and warm-boot (assertion of DEVRST_N pin or assertion of reset from the tamper macro) timing. The power-up diagrams assume all power supplies to the device are stable.

7.9.1 Power-On (Cold) Reset Initialization Sequence

The following cold reset timing diagram shows the initialization sequencing of the device.

7.9.4 Design Dependence of T_{PUFT} and T_{WRFT}

Some phases of the device initialization are user design-dependent, as the device automatically initializes certain resources to user-specified configurations if those resources are used in the design. It is necessary to compute the overall power-up to functional time by referencing the following tables and adding the relevant phases, according to the design configuration. The following equation refers to timing parameters specified in the above timing diagrams. Please note T_{PCIE}, T_{XCVR}, T_{LSRAM}, and T_{USRAM} can be found in the PolarFire FPGA device power-up and resets user guide UG0725.

$$T_{PUFT} = T_{FAB_READY(cold)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$$

$$T_{WRFT} = T_{FAB_READY(warm)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$$

Note: T_{PCIE}, T_{XCVR}, T_{LSRAM}, T_{USRAM}, and T_{CALIB} are common to both cold and warm reset scenarios.

Auto-initialization of FPGA (if required) occurs in parallel with I/O calibration. The device may be considered fully functional only when the later of these two activities has finished, which may be either one, depending on the configuration, as may be calculated from the following tables. Note that I/O calibration may extend beyond T_{PUFT} (as I/O calibration process is independent of main device power-on and is instead dependent on I/O bank supply relative power-on time and ramp times). The previous timing diagram for power-on initialization shows the earliest that I/Os could be enabled, if the I/O power supplies are powered on before or at the same time as the main supplies.

7.9.5 Cold Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the power supplies reaching the above trip point levels until the FPGA fabric is operational and the FPGA I/Os are functional for low-speed (sub 400 MHz) operation.

Table 99 • Cold Boot

Power-On (Cold) Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – T _{IN_ACTIVE(cold)}	1.17	4.51	7.84	ms
Time when weak pull-ups are enabled – T _{PU_PD_ACTIVE(cold)}	1.17	4.51	7.84	ms
Time when fabric is operational – T _{FAB_READY(cold)}	1.20	4.54	7.87	ms
Time when output pins start driving – T _{OUT_ACTIVE(cold)}	1.22	4.56	7.89	ms

7.9.6 Warm Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the negation of the warm reset event until the FPGA fabric is operational and the FPGA I/Os are functional for low-speed (sub 400 MHz) operation.

Table 100 • Warm Boot

Warm Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – T _{IN_ACTIVE(warm)}	0.91	1.76	2.62	ms
Time when weak pull-ups/pull-downs are enabled – T _{PU_PD_ACTIVE(warm)}	0.91	1.76	2.62	ms
Time when fabric is operational – T _{FAB_READY(warm)}	0.94	1.79	2.65	ms
Time when output pins start driving – T _{OUT_ACTIVE(warm)}	0.96	1.81	2.67	ms

7.9.7 Miscellaneous Initialization Parameters

In the following table, T_{FAB_READY} refers to either T_{FAB_READY(cold)} or T_{FAB_READY(warm)} as specified in the previous tables, depending on whether the initialization is occurring as a result of a cold or warm reset, respectively.

Table 104 • Flash*Freeze

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from Flash*Freeze entry command to the Flash*Freeze state	T _{FF_ENTRY}		59		μs	
The time from Flash*Freeze exit pin assertion to fabric operational state	T _{FF_FABRIC_UP}		133		μs	
The time from Flash*Freeze exit pin assertion to I/Os operational	T _{FF_IO_ACTIVE}		143		μs	

7.10 Dedicated Pins

The following section describes the dedicated pins.

7.10.1 JTAG Switching Characteristics

The following table describes characteristics of JTAG switching.

Table 105 • JTAG Electrical Characteristics

Symbol	Description	Min	Typ	Max	Unit	Condition
T _{DISU}	TDI input setup time	0.0			ns	
T _{DIHD}	TDI input hold time	2.0			ns	
T _{TMSSU}	TMS input setup time	1.5			ns	
T _{TMSHD}	TMS input hold time	1.5			ns	
F _{TCK}	TCK frequency			25	MHz	
T _{TCKDC}	TCK duty cycle	40		60	%	
T _{TDOCQ}	TDO clock to Q out			8.4	ns	C _{LOAD} = 40 pf
T _{TRSTBCQ}	TRSTB clock to Q out			23.5	ns	C _{LOAD} = 40 pf
T _{TRSTBPW}	TRSTB min pulse width	50			ns	
T _{TRSTBREM}	TRSTB removal time	0.0			ns	
T _{TRSTBREC}	TRSTB recovery time	12.0			ns	
C _{INTDI}	TDI input pin capacitance			5.3	pf	
C _{INTMS}	TMS input pin capacitance			5.3	pf	
C _{INTCK}	TCK input pin capacitance			5.3	pf	
C _{INTTRSTB}	TRSTB input pin capacitance			5.3	pf	

7.10.2 SPI Switching Characteristics

The following tables describe characteristics of SPI switching.

Table 106 • SPI Master Mode (PolarFire Master) During Programming

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{MSCK}			20	MHz	

Table 107 • SPI Master Mode (PolarFire Master) During Device Initialization

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{MSCK}			40	MHz	

Table 108 • SPI Slave Mode (PolarFire Slave)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F _{SSCK}			80	MHz	

7.10.3 SmartDebug Probe Switching Characteristics

The following table describes characteristics of SmartDebug probe switching.

Table 109 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V – 1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V – 1	Unit
Maximum frequency of probe signal	F _{MAX}	100	100	100	100	MHz
Minimum delay of probe signal	T _{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T _{Max_delay}	13	12	13	12	ns

7.10.4 DEVRST_N Switching Characteristics

The following table describes characteristics of DEVRST_N switching.

Table 110 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR _{RAMP}		10		μs	It must be a normal clean digital signal, with typical rise and fall times
DEVRST_N assert time	DR _{ASSERT}	1			μs	The minimum time for DEVRST_N assertion to be recognized
DEVRST_N de-assert time	DR _{DEASSERT}	2.75			ms	The minimum time DEVRST_N needs to be de-asserted before assertion

7.10.5 FF_EXIT Switching Characteristics

The following table describes characteristics of FF_EXIT switching.

Table 111 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF _{RAMP}		10		μs	
Minimum FF_EXIT_N assert time	FF _{ASSERT}	1			μs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	FF _{DEASSERT}	170			μs	The minimum time FF_EXIT_N needs to be de-asserted before assertion

7.11 User Crypto

The following section describes user crypto.

7.11.1 TeraFire 5200B Switching Characteristics

The following table describes TeraFire 5200B switching characteristics.

Table 112 • TeraFire F5200B Switching Characteristics

Parameter	Symbol	VDD = 1.0 V STD	VDD = 1.0 V – 1	VDD = 1.05 V STD	VDD = 1.05 V – 1	Unit	Condition
Operating frequency	F _{MAX}	189		189		MHz	–40 °C to 100 °C

7.11.2 TeraFire 5200B Throughput Characteristics

The following tables for each algorithm describe the TeraFire 5200B throughput characteristics.

Note: Throughput cycle count collected with Athena TeraFire Core and RISCv running at 100 MHz.

Table 113 • AES

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-ECB-128 encrypt ¹	128	515	1095
	64K	50157	933
AES-ECB-128 decrypt ¹	128	557	1760
	64K	48385	1524
AES-ECB-256 encrypt ¹	128	531	1203
	64K	58349	1203
AES-ECB-256 decrypt ¹	128	589	1676
	64K	56673	1671
AES-CBC-256 encrypt ¹	128	576	1169
	64K	52547	1169
AES-CBC-256 decrypt ¹	128	585	1744
	64K	48565	1652
AES-GCM-128 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1925	2740
	64K	60070	2158
AES-GCM-256 encrypt ¹ , 128-bit tag, (full message encrypted/authenticated)	128	1973	2268
	64K	60102	2151

1. With DPA counter measures.

Table 114 • GMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-GCM-256 ¹ , 128-bit tag, (message is only authenticated)	128	1863	2211
	64K	49707	2128

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